

GLF1200, GLF1201

Nano Current Power IoSmart™ Switch with True Reverse Current Blocking

Product Specification

DESCRIPTION

The GLF1200 / GLF1201 is an advanced technology fully integrated I_QSmart^{TM} load switch device with True Reverse Current Blocking (TRCB) technology and the slew rate control of the output voltage.

The GLF1200 / GLF1201 offers industry leading True Reverse Current Blocking (TRCB) performance, featuring an ultra-low threshold voltage. It minimizes reverse current flow in the event that the VOUT pin voltage exceeds the VIN voltage.

An integrated slew rate control can also enhance system reliability by mitigating bus voltage swings during switching events. Where uncontrolled switches can generate high inrush currents that result in voltage droop and/or bus reset events, the GLF slew rate control specifically limits inrush currents during turn-on to minimize voltage droop.

The GLF1200 / GLF1201 load switch device supports an industry leading wide input voltage range and helps to improve operating life and system robustness. Furthermore, one device can be used in multiple voltage rail applications which helps to simplify inventory management and reduces operating cost.

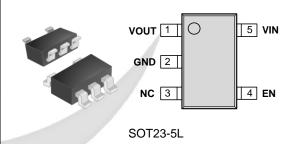
FEATURES

- True Reverse Current Blocking
- Ultra-Low I_Q : 0.47 μA Typ @ 5.5 V_{IN}
- Ultra-Low I_{SD}: 26 nA Typ @ 5.5 V_{IN}
- Low R_{ON}: 54 m Ω Typ @ 5.5 V_{IN}
- I_{OUT} Max: 2 A
- Wide Input Range: 1.5 V to 5.5 V
 - 6 V_{abs} max
- Controlled Rise Time: 600 us at 3.3 V_{IN}
- Internal EN Pull-Down Resistor on
- Integrated Output Discharge Switch: GLF1201
- HBM: 4 kV, CDM: 2 kV

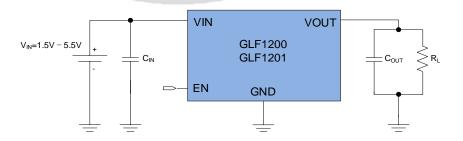
APPLICATIONS

- Low Power Subsystem
- Telecommunication Module
- Mobile Devices

PACKAGE



APPLICATION DIAGRAM



ALTERNATE DEVICE OPTIONS

Part Number	Top Mark	R _{on} (Typ) at 5.5 V _{IN}	TRCB	Output Discharge	EN Activity
GLF1200-T1G7	DM	54 mΩ	Vaa	NA	High
GLF1201-T1G7	DN	54 mΩ	Yes	85 Ω	High

FUNCTIONAL BLOCK DIAGRAM

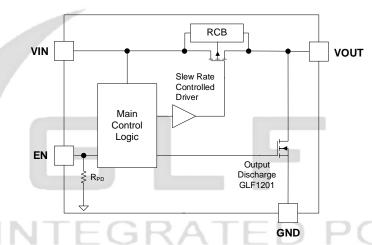


Figure 1. Functional Block Diagram

PIN CONFIGURATION

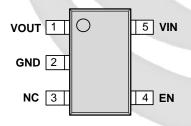


Figure 2. SOT23-5L

PIN DEFINITION

	Pin#	Name	Description			
	1	VOUT	Switch Output			
p	2	GND	Ground			
	3	NC	No connection			
	4	EN	Enable to control the switch			
	5	VIN	Switch Input. Supply Voltage for IC			

ABSOLUTE MAXIMUM RATINGS

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions; extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.

Symbol	Par	Min.	Max.	Unit	
V _{IN}	VIN, VOUT, VEN tO GND		-0.3	6	V
l _{OUT}	Maximum Continuous Switch Curre	nt		2	Α
PD	Power Dissipation at T _A = 25 °C			1.0	W
T _{STG}	Storage Junction Temperature	-65	150	°C	
T _A	Operating Temperature Range	-40	85	°C	
θјс	Thermal Resistance, Junction to Ca		90	°C/W	
θЈА	Thermal Resistance, Junction to An	nbient		180	°C/W
V _{IN}	V _{IN} , V _{OUT} , V _{EN} to GND		-0.3	6	V
		Human Body Model, JESD22-A114	4		
ESD	Electrostatic Discharge Capability	Charged Device Model, JESD22- C101	2		kV

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min.	Max.	Unit
VIN	Supply Voltage	1.5	5.5	V
TA	Ambient Operating Temperature	-40	+85	°C



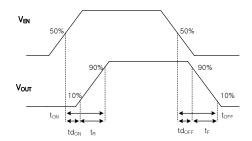
ELECTRICAL CHARACTERISTICS

Values are at $V_{IN} = 3.3V$ and $T_A = 25$ °C unless otherwise noted.

Symbol	Parameter	Conditio	ns	Min.	Тур.	Max.	Units
Basic Op	eration						
		EN = Enable, I _{OUT} =0 mA, V _{IN} = V _{EN} =5.5 V			0.47		
IQ Quiescent Current (1)		EN=Enable, I _{OUT} =0 mA, V _{IN} Ta=85 °C ⁽⁴⁾	=V _{EN} =5.5 V,		0.52		μA
		EN = Disable, Iout=0 mA, V	_{IN} =1.5 V		2.0		
		EN = Disable, Iout=0 mA, V	/ _{IN} =3.3 V		3.0		
I _{SD}	Shut Down Current	EN = Disable, I _{OUT} =0 mA, V	_{IN} =4.2 V		10		nA
130	Onat Bown ourient	EN = Disable, Iout=0 mA, V	/ _{IN} =5.5 V		26] '''
		EN = Disable, lout=0 mA, V	′ _{IN} =5.5 V, Ta=85 °C		365		
		V 55V 1 500 A	Ta=25 °C		54		
		V _{IN} =5.5 V, I _{OUT} = 500 mA	Ta=85 °C (4)		63		-
_	. 4 / . / .	V 00V 1 -00 A	Ta=25 °C		64		1
Ron	On-Resistance	V _{IN} =3.3 V, I _{OUT} = 500 mA	Ta=85 °C (4)		75		- mΩ
		V _{IN} =1.8 V, I _{OUT} = 300 mA	Ta=25 °C (4)		105		
		V _{IN} =1.5 V, I _{OUT} = 100 mA	Ta=25 °C		116		7
R _{DSC}	Output Discharge Resistance	V _{EN} =Low, I _{FORCE} = 10 mA	TED F	0	85	EF	Ω
V _{IH}	EN Input Logic High Voltage	V _{IN} =1.5 V to 5.5 V		1.2			٧
VIL	EN Input Logic Low Voltage	V _{IN} =1.5 V to 5.5 V				0.4	٧
Ren	EN Internal Resistance	Internal Pull-down Resistan	ce:		10		ΜΩ
I _{EN}	EN Current	V _{EN} =5.5 V			0.5		μA
V _{RCB_TH}	RCB Protection Threshold Voltage	Vout – Vin			35		mV
V _{RCB_RL}	RCB Protection Release Voltage	VIN — VOUT			30		mV
Switchin	g Characteristics (2, 3)						.•
t _{dON}	Turn-On Delay	D 450 0 0 0 4 v5			450		
t _R	Vout Rise Time	R_L =150 Ω, C_{OUT} =0.1 μ F			600		1
t _{dOFF}	Turn-Off Delay (4)	D 450 0 0 04 v.5 0	L E4200		17]
t⊧	Vout Fall Time (4)	R _L =150 Ω, C _{OUT} =0.1 μF : GLF1200			27		μs
tdOFF	Turn-Off Delay (4)	D. 150 O. C. 0.1 v. C. C	L F1201		17		1
tϝ	V _{OUT} Fall Time (3), (4)	R _L =150 Ω, C _{OUT} =0.1 μF : G		12		1	

Notes:

- 1. IQ does NOT include Enable pull down current through the pull-down resistor RPD.
- t_{ON} = t_{dON} + t_R, t_{OFF} = t_{dOFF} + t_F
 Output discharge path is enabled during off.
- 4. By design; characterized, not production tested.



TYPICAL PERFORMANCE CHARACTERISTICS

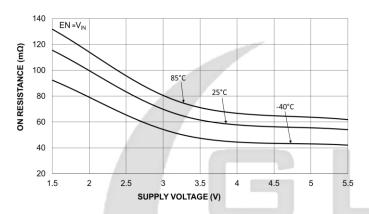


Figure 3. On-Resistance vs. Supply Voltage

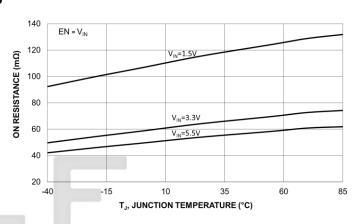


Figure 4. On-Resistance vs. Temperature

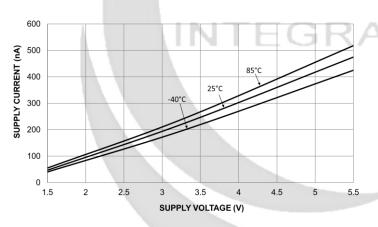


Figure 5. Quiescent Current vs. Supply Voltage

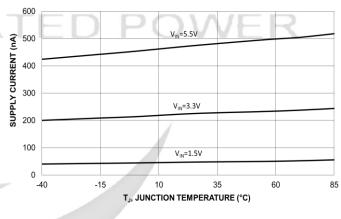


Figure 6. Quiescent Current vs. Temperature

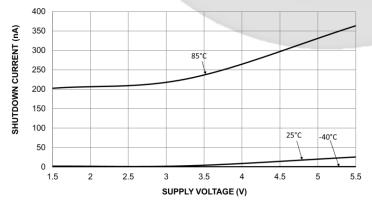


Figure 7. Shutdown Current vs. Supply Voltage

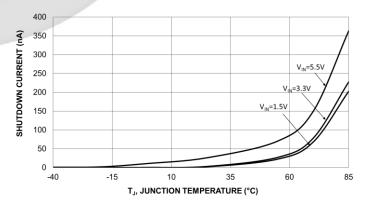
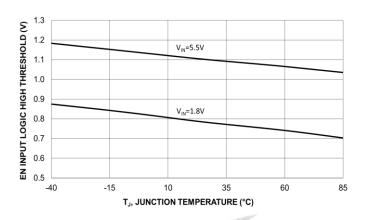


Figure 8. Shutdown Current vs. Temperature



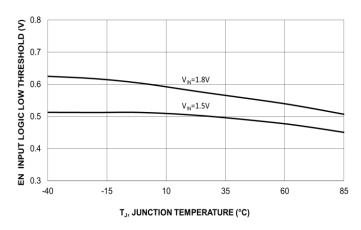
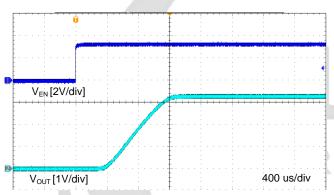


Figure 9. EN Input Logic High Threshold Vs. Temperature

Figure 10. EN Input Logic Low Threshold Vs. Temperature





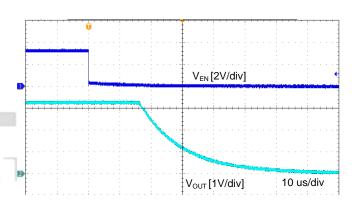


Figure 12. Turn-On Response, GLF1200 V_{IN} =3.3 V, C_{IN} =0.1 μ F, C_{OUT} =0.1 μ F, R_L =150 Ω

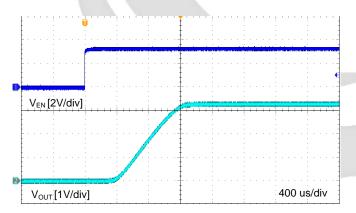


Figure 13. Turn-On Response, GLF1201 $V_{IN}=3.3 \text{ V}$, $C_{IN}=0.1 \mu F$, $C_{OUT}=0.1 \mu F$, $R_L=150 \Omega$

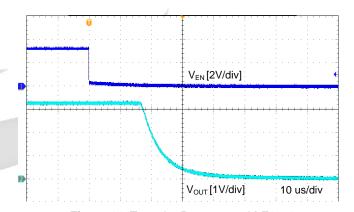
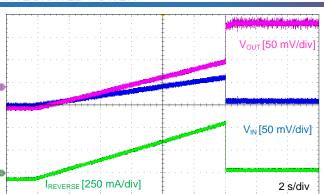


Figure 14. Turn-On Response, GLF1201 V_{IN} =3.3 V, C_{IN} =0.1 μ F, C_{OUT} =0.1 μ F, R_L =150 Ω



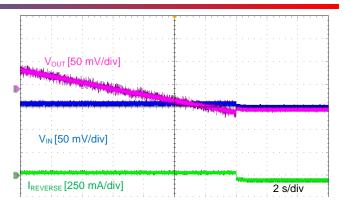


Figure 15. Reverse Current Blocking Threshold

Figure 16. Reverse Current Blocking Release

VIN=3.3 V, Vout =Up to 3.4 V in CIN=0.1 μ F, COUT=0.1 μ F, RL=150 Ω VIN=3.3 V, Vo

V_{IN}=3.3 V, Vout=Down to 3.2 V, C_{IN}=0.1 μ F, C_{OUT}=0.1 μ F, R_L=150 Ω

APPLICATION INFORMATION

The GLF1200 / GLF1201 integrated 2 A, Ultra-Efficient I_QSmart[™] Load Switch devices with a fixed slew rate control to limit the inrush current during turn on. Each device is capable of operating over a wide input range from 1.5 V to 5.5 V with very low on-resistance to reduce conduction loss. In the off state, these devices consume very low leakage current to avoid unwanted standby current and save limited input power.

Input Capacitor

The GLF1200 / GLF1201 does not require an input capacitor. However, to reduce the voltage drop on the input power rail caused by transient inrush current at start-up, a 0.1 μF capacitor is recommended to be placed close to the V_{IN} pin. A higher input capacitor value can be used to further attenuate the input voltage drop.

Output Capacitor

The GLF1200 / GLF1201 does not require an output capacitor. However, use of an output capacitor is recommended to mitigate voltage undershoot on the output pin when the switch is turning off. Undershoot can be caused by parasitic inductance from board traces or intentional load inductances. If load inductances do exist, use of an output capacitor can improve output voltage stability and system reliability. The Cout capacitor should be spaced close to the VOUT and GND pins.

EN pin

The GLF1200 / GLF1201 can be activated by forcing EN pin high level. Note that the EN pin has an internal pull-down resistor to help pull the main switch to a known "off state" when no EN signal is applied from an external controller.

True Reverse Current Blocking

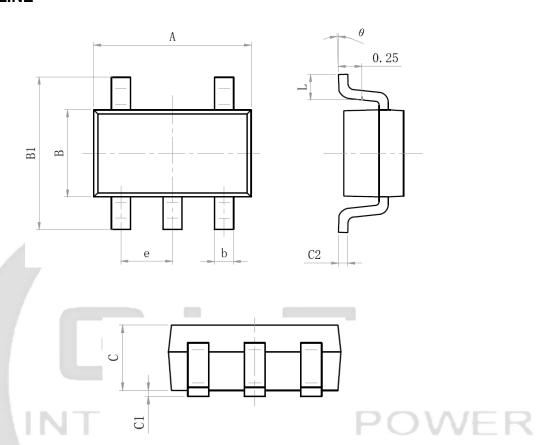
The GLF1200 / GLF1201 has a built-in reverse current blocking protection which always monitors the output voltage level regardless of the status of EN pin to check if it is greater than the input voltage. When the output voltage goes beyond the input voltage by 25 mV, that is the reverse current blocking protection trip voltage, the reverse current blocking function block turns off the switch. Note that some reverse current can occur until the V_{RCB} is triggered. The main switch will resume normal operation when the output voltage drops below the input source by the RCB protection release voltage.

Output Discharge Function

The GLF1200 / GLF1201 has an internal discharge N-channel FET switch on the VOUT pin. When EN signal turns the main power FET to an off state, the N-channel switch turns on to discharge an output capacitor quickly.



PACKAGE OUTLINE



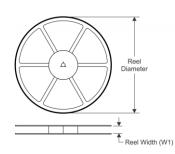
Size Mark	Min(mm)	Max(mm)	Size Mark	Min(mm)	Max(mm)
A	2.82	3.02	С	1.05	1. 15
е	0.9	95 (BSC)	C1	0.03	0.15
b	0. 28	0.45	C2	0.12	0. 23
В	1.50	1.70	L	0.35	0.55
B1	2.60	3.00	θ	0°	8°

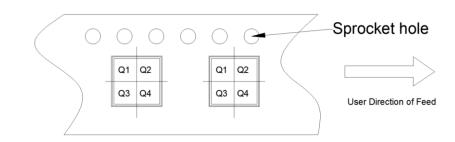


TAPE AND REEL INFORMATION

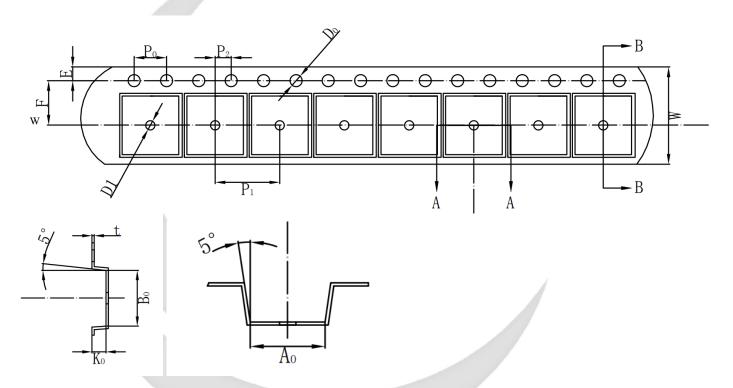
REEL DIMENSIONS

QUADRANT ASSIGNMENTS PIN 1 ORIENTATION TAPE





TAPE DIMENSIONS



Device	Package	Pins	SPQ	Reel Diameter (mm)	Reel Width W1	Α0	В0	K0	P1	W	Pin1
GLF1200-T1G7	SOT23-5	5	3000	178	9	3.25	3.30	1.38	4	8	Q3
GLF1201-T1G7	SOT23-5	5	3000	178	9	3.25	3.30	1.38	4	8	Q3

Remark:

- A0: Dimension designed to accommodate the component width
- B0: Dimension designed to accommodate the component length
- C0: Dimension designed to accommodate the component thickness
- W: Overall width of the carrier tape
- P1: Pitch between successive cavity centers



GLF1200, GLF1201

SPECIFICATION DEFINITIONS

Document Type	Meaning	Product Status
Target Specification	This is a target specification intended to support exploration and discussion of critical needs for a proposed or target device. Spec limits including typical, minimum, and maximum values are desired, or target, limits. GLF reserves the right to change limits at any time without warning or notification. A target specification in no way guarantees future production of the device in question.	Design / Development
Preliminary Specification	This is a draft version of a product specification. The specification is still under internal review and subject to change. GLF reserves the right to change the specification at any time without warning or notification. A preliminary specification in no way guarantees future production of the device in question.	Qualification
Product Specification	This document represents the anticipated production performance characteristics of the device.	Production

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